

In re Patent Application of

Serial No.

For: A SEMICONDUCTOR DEVICE AND A METHOD OF
MANUFACTURING THE SAME

Commissioner for Patents
Washington, D.C. 20231

Prior to the examination thereof, please amend the above-identified application as follows.

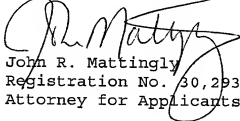
Please rewrite claim 14 as set forth below.

14. (Amended) The semiconductor device according to claim 11, wherein the epitaxial layer is comprised mainly of silicon-germanium, silicon-germanium-carbon, or silicon.

REMARKS

Claim 14 has been amended to remove its multiple dependency. Examination is respectfully requested.

Respectfully submitted,


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MARKED UP VERSION OF REWRITTEN CLAIMS

14. (Amended) The semiconductor device according to claim 11 [or claim 12], wherein the epitaxial layer is comprised mainly of silicon-germanium, silicon-germanium-carbon, or silicon.

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